

Features

- Quad micro power op amp
- Wide range of supply voltage: 1.6V~5.5V
- High input impedance
- Single supply operation
- Low current consumption: < 5 μ A per amp
- Rail to rail output
- Provides both sink and source output drive capability
- Common mode input extends below negative rail
- Pin compatible with LM324/WT274 (14-pin DIP)
- 14-pin DIP/SOP package

Applications

- Battery powered system
- Sensor amplifier
- Low power gain blocks
- Low power comparators
- Signal detectors
- Active filters
- Caller ID systems
- Communication systems

General Description

The HT9274 is a CMOS quad micro-power operational amplifier featuring high input impedance, extremely low power, high gain and high stability.

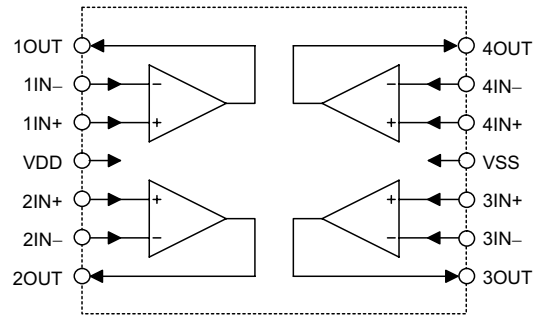
It allows common mode input voltage range which extends below the negative rail, output swings to both rails with a reasonable sink and source capability of the output drive current. This cost-effective device is suitable for high

gain, low frequency, low power applications, especially ideal for battery powered systems where μ A range of standby current is essential for long battery life span. For example, in multi-standard Caller ID systems, HT9274 is ideal as a low power line signal monitor/detector, and in car alarm systems, the HT9274 is excellent for piezo vibratile detector signal amplifier application.

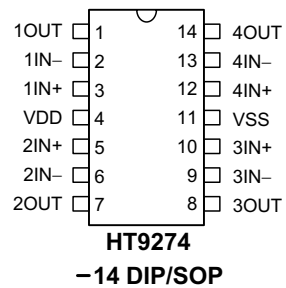
Comparison Table

ITEM	Operating Voltage	Operating Current	Output Source Current	Output Sink Current	Input Bias Current	GBW	Max. load (To VDD or VSS)
HT9274	1.6~5.5V	5 μ A	500 μ A	500 μ A	1pA	0.1MHz	>10k Ω
WT274	1.35~10V	9 μ A	16 μ A	2mA	1pA	0.1MHz	>500k Ω
LM324	3~32V	400 μ A	20mA	8mA	45nA	1MHz	>2k Ω

Block Diagram



Pin Assignment



Pin Description

Pin No.	Pin Name	I/O	Internal Connection	Description
1	1OUT	O	CMOS OUT	Output pin of the op amp 1
2	1IN–	I	PMOS IN	Inverting input pin of the op amp 1
3	1IN+	I	PMOS IN	Noninverting input pin of the op amp 1
4	VDD	—	—	Positive power supply
5	2IN+	I	PMOS IN	Noninverting input pin of the op amp 2
6	2IN–	I	PMOS IN	Inverting input pin of the op amp 2
7	2OUT	O	CMOS OUT	Output pin of the op amp 2
8	3OUT	O	CMOS OUT	Output pin of the op amp 3
9	3IN–	I	PMOS IN	Inverting input pin of the op amp 3
10	3IN+	I	PMOS IN	Noninverting input pin of the op amp 3
11	VSS	—	—	Negative power supply
12	4IN+	I	PMOS IN	Noninverting input pin of the op amp 4
13	4IN–	I	PMOS IN	Inverting input pin of the op amp 4
14	4OUT	O	CMOS OUT	Output pin of the op amp 4

Absolute Maximum Ratings

Supply Voltage–0.3V to 6V Storage Temperature.....–50°C to 125°C
 Input Voltage $V_{SS}-0.3V$ to $V_{DD}+0.3V$ Operating Temperature–20°C to 75°C

Note: These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

Electrical Characteristics
 $T_a=25^{\circ}\text{C}$

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
		V_{DD}	Conditions				
V_{OS}	Input Offset Voltage	5V	$V_o=1.4V$	—	—	5	mV
$\Delta V_{OS}/\Delta T$	Temperature Coefficient of V_{OS}	5V	—	—	2	—	$\mu\text{V}/^{\circ}\text{C}$
I_{OS}	Input Offset Current	5V	$V_i=V_o=1.4V$ $-20^{\circ}\text{C}<T_a<75^{\circ}\text{C}$	—	1	100	pA
I_b	Input Bias Current	5V	$V_i=V_o=1.4V$ $-20^{\circ}\text{C}<T_a<75^{\circ}\text{C}$	—	1	150	pA
V_{OUT+}	Positive Output Voltage Swing	5V	$R_L=1M\Omega$ $V_{IN+}-V_{IN-}\geq 10\text{mV}$	4.9	4.95	—	V
V_{OUT-}	Negative Output Voltage Swing	5V	$R_L=1M\Omega$ $V_{IN-}-V_{IN+}\geq 10\text{mV}$	—	0.01	0.05	V
A_{VOL}	Large Signal Voltage Gain	5V	$V_i=1.4V$ $R_L=1M\Omega$ $V_o=1$ to $4V$	20	200	—	V/mV
GBW	Gain Band Width Product	5V	$R_L=1M\Omega$ $C_L=100\text{pF}$	—	0.1	—	MHz
CMRR	Common Mode Rejection Ratio	5V	$V_o=1.4V$ $V_i=0V$	60	80	—	dB
PSRR	Power Supply Rejection Ratio	1.8~5V	$V_o=1.4V$	60	80	—	dB
I_{CC}	Supply Current Per Single Amplifier	5V	$A_v=1$ $V_o=1.4V$ No load	—	3	5	μA
SR	Slew Rate at Unity Gain	5V	No load	—	0.03	—	V/ μs
Φ_m	Phase Margin at Unity Gain	5V	$R_L=1M\Omega$ $C_L=100\text{pF}$	—	55	—	Degree
e_n	Input Equivalent Noise Voltage	5V	$f=1\text{kHz}$ $R_S=10\Omega$	Σ	50	Σ	$\text{nV}/\sqrt{\text{Hz}}$
V_{O1}/V_{O2}	Cross Talk Attenuation	5V	—	—	100	—	dB
I_{OH}	Output Source Current	5V	$V_{IN+}-V_{IN-}\geq 10\text{mV}$	-300	-500	—	μA
I_{OL}	Output Sink Current	5V	$V_{IN-}-V_{IN+}\geq 10\text{mV}$	300	500	—	μA

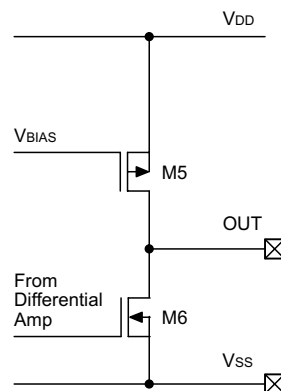
Input stage

The diagram shows a differential amplifier circuit. The input stage consists of two NMOS transistors, M1 and M2, whose sources are connected to a common source node. M1's gate is connected to the Noninverting In input, and M2's gate is connected to the Inverting In input. The drains of M1 and M2 are connected to a PMOS current source load, which is implemented as a PMOS transistor M3. The gates of M3 and M4 are connected to VDD, and their sources are connected to the common source node. The drain of M3 is connected to VDD, and the drain of M4 is connected to the output node, which is labeled 'To Output Stage'. The gates of M5 and M6 are connected to VDD, and their sources are connected to VSS. The gates of M7 and M8 are connected to VDD, and their sources are connected to VSS. The gates of M9 and M10 are connected to VDD, and their sources are connected to VSS.

Actually the extremely high input impedance is its major advantage over the bipolar counterpart, in some application fields such as integrators where the input current of op amp can cause significant error, the HT9274 is a better choice than the popular LM324.

Output stage

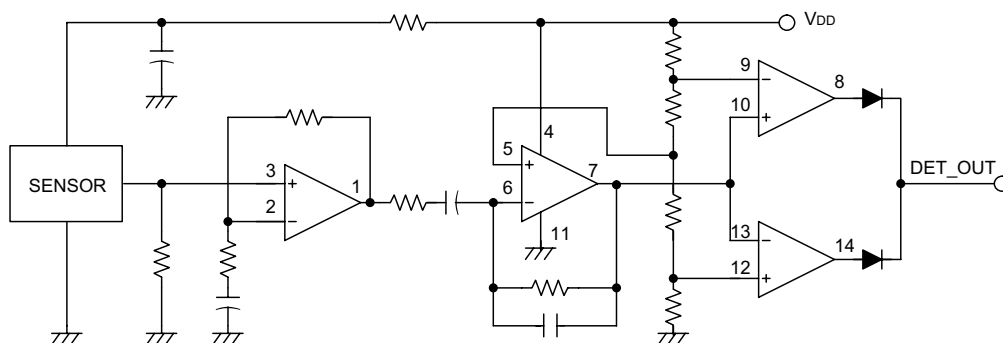
Note that the output is an unbuffered structure, therefore the open loop gain will be affected by the load resistor since the voltage gain of this stage can be expressed as $(g_{m5} + g_{m6}) \times R_{L1}$.



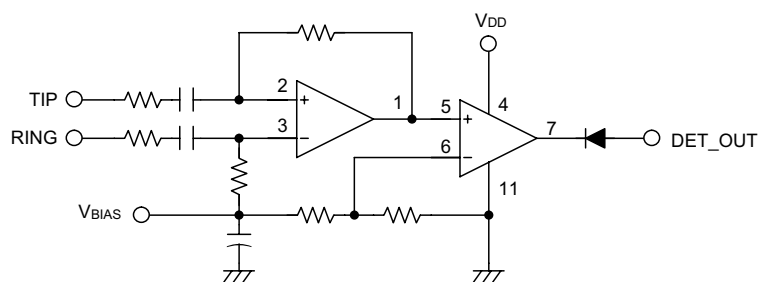
The HT9274 is internally compensated for AC stability and capable to withstand up to a 100pF capacitive load.

Application Circuits

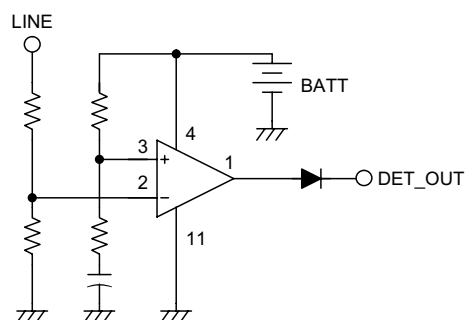
Micro power sensor amplifier & detector



Micro power line signal monitor



Micro power line voltage monitor



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